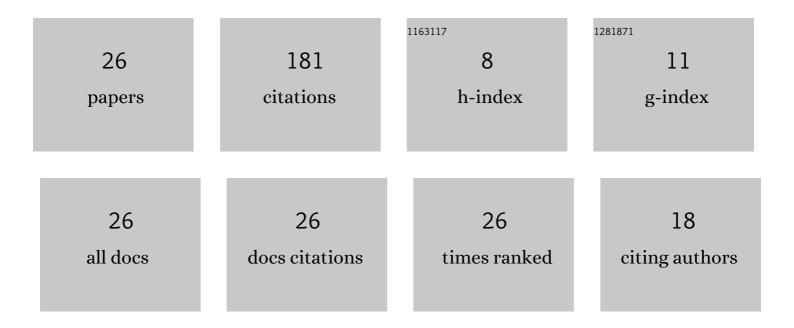
Sergei Chebotarev

List of Publications by Year in descending order

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#	Article	IF	CITATIONS
1	DEVELOPMENT OF TECHNOLOGY FOR PRODUCTION OF SOFT CHEESE PRODUCT BASED ON THREE-COMPONENT RAW MATERIAL MIXTURE. Vestnik VostoÄno-Sibirskogo Gosudarstvennogo Universiteta Tehnologij I Upravleniâ, 2021, , 5-12.	0.2	0
2	Technology of production of kumis drink enriched with iodine-glycosideÂcomplex. Vestnik Voronežskogo Gosudarstvennogo Universiteta inženernyh Tehnologij, 2021, 83, 137-142.	0.3	0
3	Wireless software-hardware complex for testing semiconductor structures. Journal of Physics: Conference Series, 2019, 1410, 012202.	0.4	0
4	Simulation of electrical conductivity of silicon diodes with bismuth implanted-ion profiles. Journal of Physics: Conference Series, 2018, 1124, 071009.	0.4	1
5	Features of a zone thermal crystallization semiconductor thin films grown from a discrete liquid source. Journal of Physics: Conference Series, 2018, 1124, 022015.	0.4	0
6	Variation of the photoluminescence spectrum of InAs/GaAs heterostructures grown by ion-beam deposition. Beilstein Journal of Nanotechnology, 2018, 9, 2794-2801.	2.8	4
7	Study of the Structural and Luminescence Properties of InAs/GaAs Heterostructures with Bi-Doped Potential Barriers. Semiconductors, 2018, 52, 729-733.	0.5	3
8	Investigation of the Structural Perfection of Thin-Film InAlGaPAs/GaAs Heterostructures. Journal of Surface Investigation, 2018, 12, 466-472.	0.5	1
9	Effect of bismuth on parameters of a GalnSbAsP solid solution grown on GaSb substrates. Inorganic Materials, 2017, 53, 57-64.	0.8	5
10	Synthesis and properties of InxAlyGa1–x–yPzAs1–z/GaAs heterostructures. Inorganic Materials, 2017, 53, 1217-1227.	0.8	14
11	Thin-layer GalnSbAsPBi/GaSb heterostructures obtained from liquid phase in a temperature-gradient field. Crystallography Reports, 2017, 62, 139-143.	0.6	2
12	Germanium layers grown by zone thermal crystallization from a discrete liquid source. Journal of Physics: Conference Series, 2017, 917, 032008.	0.4	5
13	Obtaining and doping of InAs-QD/GaAs(001) nanostructures by ion beam sputtering. Beilstein Journal of Nanotechnology, 2017, 8, 12-20.	2.8	10
14	Morphology and Optical Investigations of InAs-QD/GaAs Heterostructures Obtained by Ion-Beam Sputtering. Journal of Nanotechnology, 2016, 2016, 1-9.	3.4	7
15	Specific features of doping with antimony during the ion-beam crystallization of silicon. Semiconductors, 2016, 50, 545-548.	0.5	4
16	Regularities of ion-beam-induced crystallization and properties of InAs-QD/GaAs(001) semiconductor nanoheterostructures. Nanotechnologies in Russia, 2016, 11, 435-443.	0.7	11
17	Growth and properties of GalnPSbAs isoperiodic solid solutions on indium arsenide substrates. Physics of the Solid State, 2016, 58, 1751-1757.	0.6	5
18	Ion beam crystallization of InAs/GaAs(001) nanostructures. Technical Physics Letters, 2015, 41, 661-664.	0.7	17

SERGEI CHEBOTAREV

#	Article	IF	CITATIONS
19	Carrier transport in multilayer InAs/GaAs quantum dot heterostructures grown by ion beam crystallization. Inorganic Materials, 2015, 51, 197-200.	0.8	5
20	Correlation between the size and photoluminescence spectrum of quantum dots in InAs-QD/GaAs. Journal of Surface Investigation, 2013, 7, 36-40.	0.5	12
21	Features in the formation of Ge/Si multilayer nanostructures under ion-beam-assisted crystallization. Technical Physics Letters, 2013, 39, 726-729.	0.7	12
22	Structure of Ge nanoclusters grown on Si(001) by ion beam crystallization. Inorganic Materials, 2013, 49, 435-438.	0.8	11
23	Ion beam deposition of photoactive nanolayers for silicon solar cells. Inorganic Materials, 2012, 48, 439-444.	0.8	14
24	Photoluminescence of i-Ga x In1 â^' x As/n-GaAs heterostructures containing a random InAs quantum dot array. Inorganic Materials, 2011, 47, 816-818.	0.8	13
25	A study of photosensitive InAs/GaAs heterostructures with quantum dots grown by ion-beam deposition. Journal of Surface Investigation, 2011, 5, 559-562.	0.5	12
26	Formation and use of positioning marks in scanning probe microscopy. Technical Physics Letters, 2010, 36, 737-738.	0.7	13